Dual Low-Voltage CMOS 2-to-4 Decoder/Demultiplexer

With 5V–Tolerant Inputs

The MC74LCX139 is a high performance, 2-to-4 decoder/ demultiplexer operating from a 2.3 to 3.6 V supply. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5 V allows MC74LCX139 inputs to be safely driven from 5 V devices. The MC74LCX139 is suitable for memory address decoding and other TTL level bus oriented applications.

The MC74LCX139 high-speed 2-to-4 decoder/demultiplexer accepts two binary weighted inputs (A0, A1) and, when enabled, provides four mutually exclusive active-LOW outputs. The LCX139 features an active low Enable input. All outputs will be HIGH unless En is LOW. The LCX139 can be used as an 8-output demultiplexer by using one of the active-LOW Enable inputs as the data input and the other Enable input as a strobe. The Enable inputs which are not used must be permanently tied to ground.

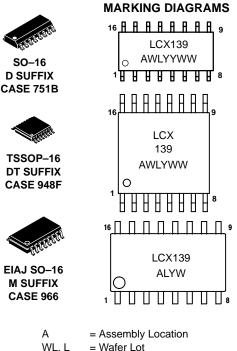
Current drive capability is 24 mA at the outputs.

- Designed for 2.3 to 3.6 V V_{CC} Operation
- 5 V Tolerant Inputs Interface Capability With 5 V TTL Logic
- LVTTL Compatible
- LVCMOS Compatible
- 24 mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current (10 µA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500 mA
- ESD Performance: Human Body Model >2000 V; Machine Model >200 V



ON Semiconductor

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= Wafer Lot

YY, Y = Year WW, W = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74LCX139D	SO-16	48 Units/Rail
MC74LCX139DR2	SO–16	2500 Units/Reel
MC74LCX139DT	TSSOP-16	96 Units/Rail
MC74LCX139DTEL	TSSOP-16	2000 Units/Reel
MC74LCX139DTR2	TSSOP-16	2000 Units/Reel
MC74LCX139M	EIAJ SO-16	48 Units/Rail
MC74LCX139MEL	EIAJ SO-16	2000 Units/Reel

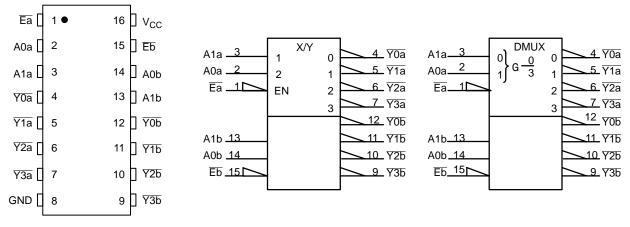


Figure 1. Pin Assignment

Figure 2. IEC Logic Diagram

PIN NAMES

Pins	Function
A0n–A1n	Address Inputs
En	Enable Inputs
<u>Y0</u> n– <u>Y3</u> n	Outputs

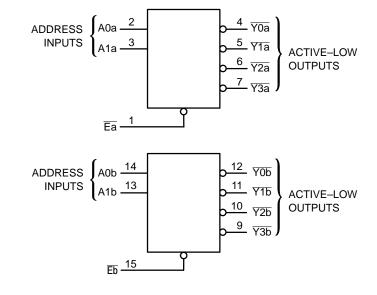
TRUTH TABLE

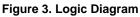
	Inputs	3		Out	puts	
E	A1	A0	YO	<u>Y1</u>	<u>Y2</u>	<u>Y3</u>
Н	Х	Х	н	Н	Н	Н
L	L	L	L	Н	н	Н
L	L	н	н	L	Н	Н
L	н	L	н	Н	L	Н
L	н	Н	н	Н	Н	L

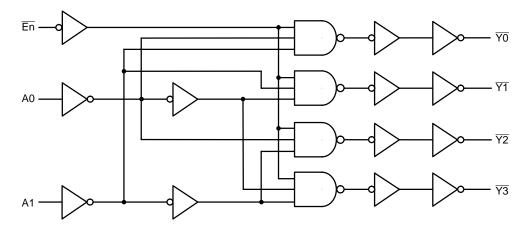
H = High Voltage Level;

L = Low Voltage Level;

Z = High Impedance State









MAXIMUM RATINGS

Symbol	Parameter	Value	Condition	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \le V_I \le +7.0$		V
Vo	DC Output Voltage	$-0.5 \le V_O \le V_{CC} + 0.5$	Output in HIGH or LOW State. (Note 1)	V
I _{IK}	DC Input Diode Current	-50	V _I < GND	mA
I _{ОК}	DC Output Diode Current	-50	V _O < GND	mA
		+50	V _O > V _{CC}	mA
Ι _Ο	DC Output Source/Sink Current	±50		mA
I _{CC}	DC Supply Current Per Supply Pin	±100		mA
I _{GND}	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum–rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

1. I_O absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Тур	Max	Unit
V _{CC}	Supply Voltage Data Rete	Operating ention Only	2.0 1.5	2.3 to 3.3	3.6 3.6	V
VI	Input Voltage		0		5.5	V
Vo	Output Voltage (HIGH or L	OW State)	0		V _{CC}	V
I _{OH}	$V_{CC} = 2.1$	0 V - 3.6 V 7 V - 3.0 V 3 V - 2.7 V			-24 -12 -8	mA
I _{OL}	$V_{\rm CC} = 2.7$	0 V - 3.6 V 7 V - 3.0 V 3 V - 2.7 V			+24 +12 +8	mA
T _A	Operating Free-Air Temperature		-40		+85	°C
$\Delta t / \Delta V$	Input Transition Rise or Fall Rate, V_{IN} from 0.8 V to 2.0	V, V _{CC} = 3.0 V	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

			T _A = −40°C	to +85°C	
Symbol	Characteristic	Condition	Min	Мах	Unit
VIH	HIGH Level Input Voltage (Note 2)	$2.3~\textrm{V} \leq \textrm{V}_{\textrm{CC}} \leq 2.7~\textrm{V}$	1.7		V
		$2.7 \text{ V} \leq \text{V}_{\text{CC}} \leq 3.6 \text{ V}$	2.0		
VIL	LOW Level Input Voltage (Note 2)	$2.3 \text{ V} \leq \text{V}_{\text{CC}} \leq 2.7 \text{ V}$		0.7	V
		$2.7 \text{ V} \leq \text{V}_{\text{CC}} \leq 3.6 \text{ V}$		0.8	
V _{OH}	HIGH Level Output Voltage	2.3 V \leq V_{CC} \leq 3.6 V; I_{OL} = 100 μA	V _{CC} - 0.2		V
		V _{CC} = 2.3 V; I _{OH} = -8 mA	1.7		
		$V_{CC} = 2.7 \text{ V}; I_{OH} = -12 \text{ mA}$	2.2		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -18 \text{ mA}$	2.4		
		$V_{CC} = 3.0 \text{ V}; I_{OH} = -24 \text{ mA}$	2.2		
V _{OL}	LOW Level Output Voltage	2.3 V \leq V_{CC} \leq 3.6 V; I_{OL} = 100 μA		0.2	V
		V _{CC} = 2.3 V; I _{OL} = 8 mA		0.7	
		V _{CC} = 2.7 V; I _{OL} = 12 mA		0.4	
		V _{CC} = 3.0 V; I _{OL} = 16 mA		0.4	
		$V_{CC} = 3.0 \text{ V}; \text{ I}_{OL} = 24 \text{ mA}$		0.55	
I _I	Input Leakage Current	$2.3 \text{ V} \leq \text{V}_{CC} \leq 3.6 \text{ V}; 0 \text{ V} \leq \text{V}_{I} \leq 5.5 \text{ V}$		±5	μΑ
I _{CC}	Quiescent Supply Current	$2.3 \leq V_{CC} \leq 3.6$ V; VI = GND or V_{CC}		10	μΑ
		$2.3 \leq V_{CC} \leq 3.6$ V; $3.6 \leq V_{I}$ or $V_{O} \leq 5.5$ V		±10	
ΔI_{CC}	Increase in I _{CC} per Input	$2.3 \le V_{CC} \le 3.6$ V; $V_{IH} = V_{CC} - 0.6$ V		500	μA

2. These values of V_I are used to test DC electrical characteristics only.

AC CHARACTERISTICS t_R = t_F = 2.5 ns; C_L = 50 pF; R_L = 500 Ω

				Lin	nits			
				T _A = −40°C	C to +85°C			
		V _{CC} = 3.0	V to 3.6 V	V _{CC} =	2.7 V	V _{CC} = 2.3	V to 2.7 V	
		C _L = 5	50 pF	C _L = 5	50 pF	C _L = 3	30pF	
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Unit
t _{PLH}	Propagation Delay	0.8	6.2	1.0	7.3	0.8	9.3	ns
t _{PHL}	A to Y	0.8	6.2	1.0	7.3	0.8	9.3	ns
t _{PLH}	Propagation Delay	0.8	4.7	1.0	5.2	0.8	7.2	ns
t _{PHL}	E to Y	0.8	4.7	1.0	5.2	0.8	7.2	ns
t _{OSHL}	Output-to-Output Skew		1.0					ns
tOSLH	(Note 3)		1.0					ns

 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t_{OSHL}) or LOW-to-HIGH (t_{OSLH}); parameter guaranteed by design.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	7	pF
C _{OUT}	Output Capacitance	V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10MHz, V_{CC} = 3.3 V, V_{I} = 0 V or V_{CC}	25	pF

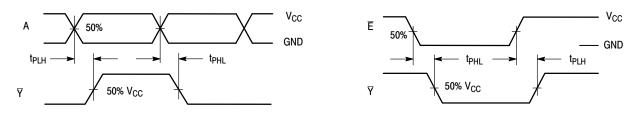
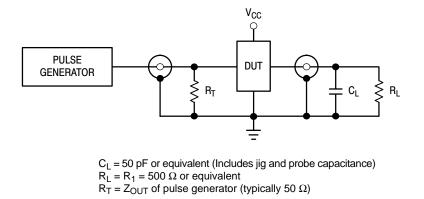


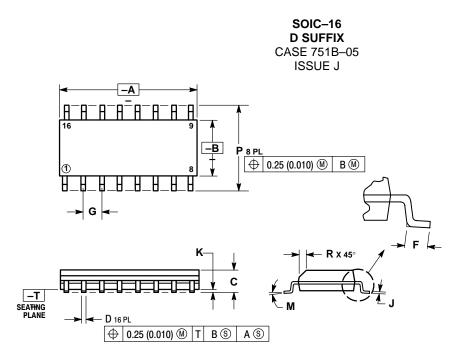
Figure 5. Waveform 1 Prop Delays

Figure 6. Waveform 2 Output Enable





PACKAGE DIMENSIONS

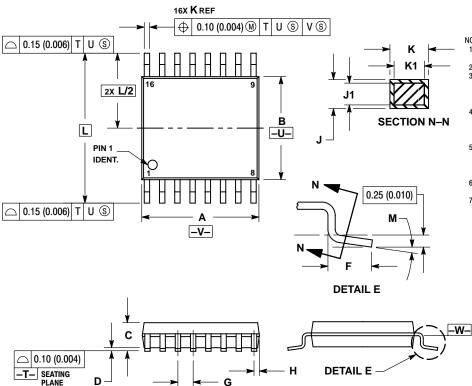


NOTES:

- THESE DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. 1.
- 3.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) 4. PER SIDE.
- PROTRUSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT 5. MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
С	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.2	7 BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
М	0°	7 °	0°	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

TSSOP-16 DT SUFFIX CASE 948F-01 ISSUE O



G

D

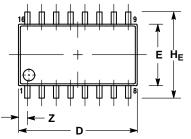
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 1.
- 2.
- Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER 3. SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD 4. FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- 0.25 (0.010) PER SIDE. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION. 5.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 6.
 - DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
Κ	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40 BSC		0.252 BSC		
М	0 °	8°	0°	8°	

PACKAGE DIMENSIONS

SOIC EIAJ-16 **M SUFFIX** CASE 966-01 **ISSUE O**

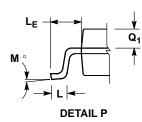


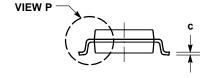
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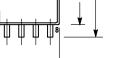
0.13 (0.005) 🕅





- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α		2.05		0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
C	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
е	1.27	BSC	0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LΕ	1.10	1.50	0.043	0.059
Μ	0 °	10 °	0 °	10 °
Q ₁	0.70	0.90	0.028	0.035
Z		0.78		0.031



Α

A₁



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